CMOS 8-Bit Microcontroller

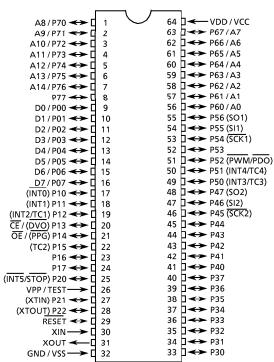
## **TMP87PH00N** TMP87PH00F TMP87PH00DF TMP87PH00LF

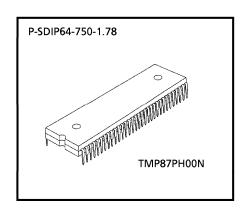
The 87PH00 is a One-Time PROM microcontroller with low-power 128 K bits (16 Kbytes) electrically programmable read only memory for the 87C800/CH00 system evaluation. The 87PH00 is pin compatible with the 87C800/CH00. The operations possible with the 87C800/CH00 can be performed by writing programs to PROM. The 87PH00 can write and verify in the same way as the TMM27256AD using an adaptor socket BM1136/BM1137/BM1173 and an EPROM programmer.

Part No.	OTP	RAM	Package	Adapter Socket
TMP87PH00N			P-SDIP64-750-1.78	BM1136
TMP87PH00F	16 K × 8-bit	2560 hit	P-QFP64-1420-1.00A	BM1137
TMP87PH00DF	IO K X 8-DIT	256 × 8-bit	D 05DS4 4444 0 004	DN44472
TMP87PH00LF			P-QFP64-1414-0.80A	BM1173

## Pin Assignments (Top View)

P-SDIP64-750-1.78





For a discussion of how the reliability of microcontrollers can be predicted, please refer to Section 1.3 of the chapter entitled Quality and Reliability

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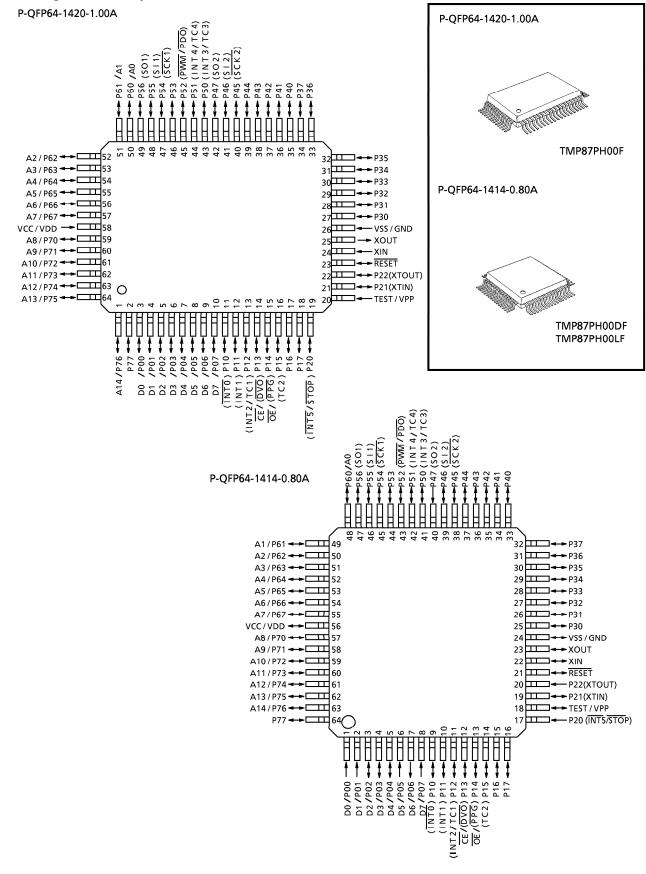
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# Pin Assignments (Top View)



## **Pin Function**

The 87PH00 has two modes: MCU and PROM.

(1) MCU mode
In this mode, the 87PH00 is pin compatible with the 87C800/CH00 (fix the TEST pin at low level).

## (2) PROM mode

Pin Name (PROM mode)	Input/Output	Functions	Pin Name (MCU mode)			
A14 to A8  A7 to A0	Input	PROM address inputs	P76 to P70 P67 to P60			
D7 to D0	I/O	PROM data input/outputs	P07 to P00			
CE		Chip enable signal input (active low)	P13			
ŌĒ	Input	Output enable signal input (active low)	P14			
VPP		+ 12.5 V / 5 V (Program supply voltage)	TEST			
vcc	Power supply	+5V	VDD			
GND		ov	VSS			
P37 to P30						
P47 to P40		Pull-up with resistance for input processing				
P56 to P50						
P11						
P21	I/O	PROM mode setting pin. Be fixed at high level.				
P77						
P17 to P15						
P12, P10		PROM mode setting pin. Be fixed at low level.				
P22, P20		Thom mode setting pin. Be fixed acrow level.				
RESET						
XIN	Input	Connect an 8MHz oscillator to stabilize the internal state.				
XOUT	Output					

## **Operational Description**

The following explains the 87PH00 hardware configuration and operation. The configuration and functions of the 87PH00 are the same as those of the 87C800/CH00, except in that a one-time PROM is used instead of an on-chip mask ROM.

The 87PH00 is placed in the *single-clock* mode during reset. To use the dual-clock mode, the low-frequency oscillator should be turned on by executing [SET (SYSCR2). XTEN] instruction at the beginning of the program.

## 1. Operating Mode

The 87PH00 has two modes: MCU and PROM.

#### 1.1 MCU mode

The MCU mode is activated by fixing the TEST / VPP pin at low level.

In the MCU mode, operation is the same as with the 87C800/CH00 (the TEST / VPP pin cannot be used open because it has no built-in pull-down resistance).

#### 1.1.1 Program Memory

The 87PH00 has a 16 K  $\times$  8-bit (addresses C000<sub>H</sub> to FFFF<sub>H</sub> in the MCU mode, addresses 4000<sub>H</sub> to 7FFF<sub>H</sub> in the PROM mode) of program memory (OTP).

To use the 87PH00/PH00L as the system evaluation for the 87C800/CH00/CH00L, the program should be written to the program memory area as shown in Figure 1-1.

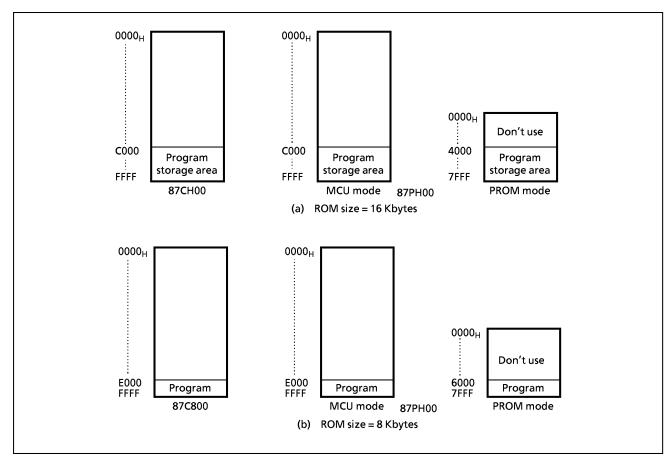


Figure 1-1. Program Memory Area

Note: Either write the data FFH to the unused area or set the PROM programmer to access only the program storage area.

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## 1.1.2 Data Memory

The 87PH00 has an on-chip 256  $\times$  8-bit data memory (static RAM).

## 1.1.3 Input/Output Circuitry

## (1) Control pins

The control pins of the 87PH00 are the same as those of the 87C800/CH00 except that the TEST pin has is no built-in pull-down resistance.

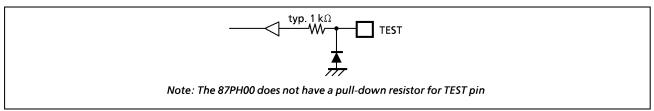


Figure 1-2. TEST Pin

## (2) I/O ports

The I/O circuitries of 87PH00 I/O ports the are the same as the code A type I/O circuitries of the 87C800/CH00.

When using as an evaluator of other I/O codes (C, D, G), external pull-up resistors are required.

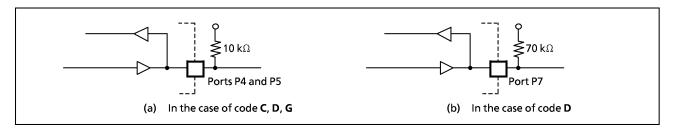


Figure 1-3. I/O Circuitry Code and External Circuitry

#### 1.2 PROM Mode

The PROM mode is activated by setting the TEST, RESET pin and the ports P17 to P10, P22 to P20 and P77 as shown in Figure 1-4. The PROM mode is used to write and verify programs with a general-purpose PROM programmer. The high-speed programming mode can be used for program operation. The 87PH00 is not supported an electric signature mode, so the ROM type must be set to TC57256 AD. Set the adaptor socket switch to "P".

Note: Please set the high-speed programing mode according to each manual of PROM programmer.

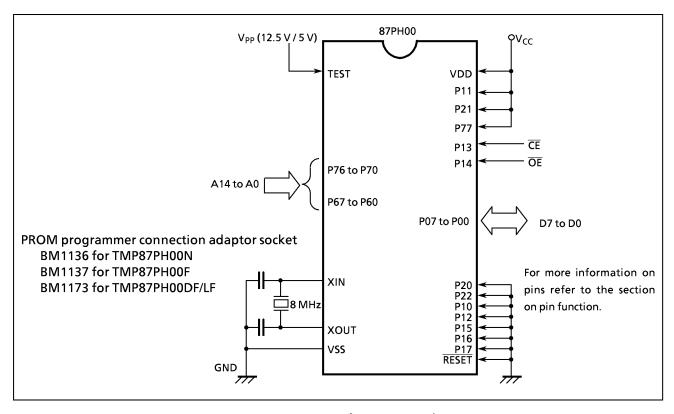


Figure 1-4. Setting for PROM Mode

## 1.2.1 Programming Flowchart (High-speed Programming Mode-I)

The high-speed programming mode is achieved by applying the program voltage (  $\pm$  12.5 V) to the Vpp pin when Vcc = 6 V. After the address and input data are stable, the data is programmed by applying a single 1ms program pulse to the  $\overline{CE}$  input. The programmed data is verified. If incorrect, another 1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. Programming for one address is ended by applying additional program pulse with width 3 times that needed for initial programming (number of programmed times  $\times$  1 ms). After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.

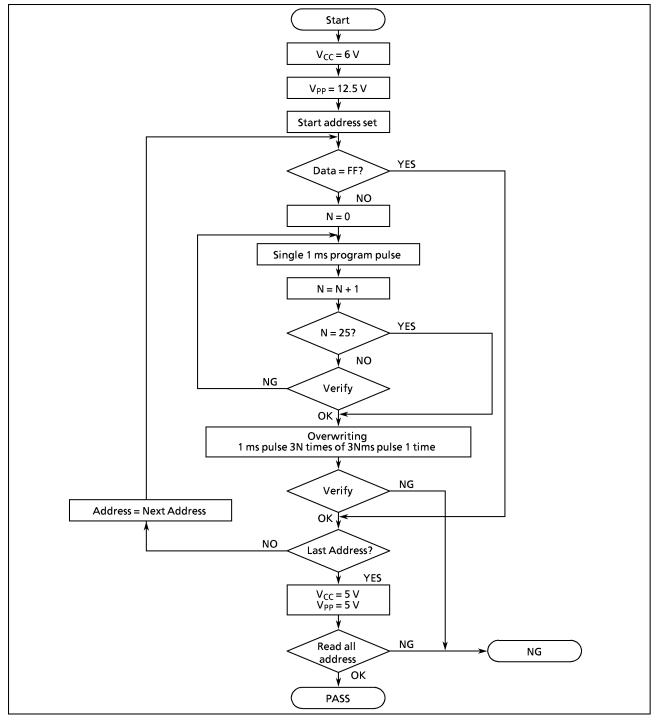


Figure 1-5. Flowchart of High-speed Programming Mode - I

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## 1.2.2 Programming Flowchart (High-speed Programming Mode-II)

The high-speed programming mode is achieved by applying the program voltage (  $\pm$  12.75 V) to the Vpp pin when Vcc = 6.25 V. After the address and input data are stable, the data is programmed by applying a single 0.1ms program pulse to the  $\overline{CE}$  input. The programmed data is verified. If incorrect, another 0.1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.

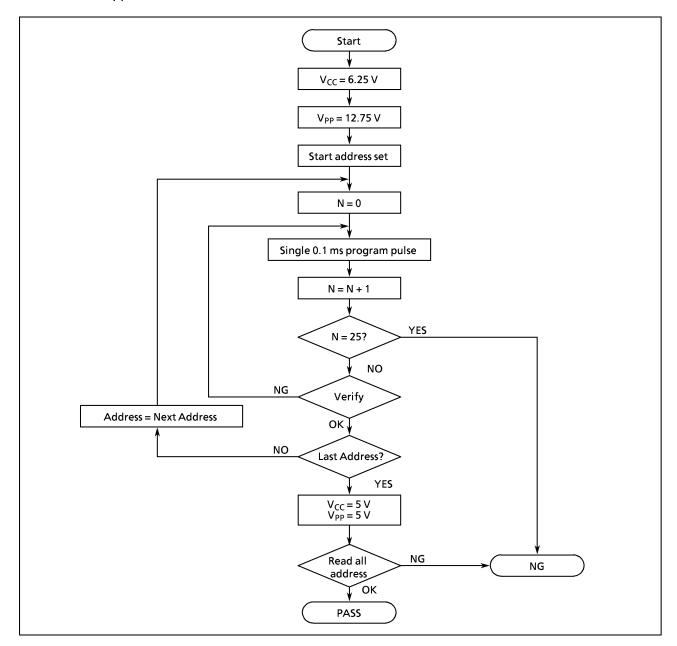


Figure 1-6. Flowchart of High-speed Programming Mode - II

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# 1.2.3 Writing method for general-purpose PROM program

(1) Adapters

BM1136: TMP87PH00N BM1137: TMP87PH00F

BM1173: TMP87PH00DF, 87PH00LF

(2) Adapter setting Switch (SW1) is set to side N.

- (3) PROM programmer specifying
  - i) PROM type is specified to TC57256AD.

Writing voltage: 12.5 V (high-speed program I mode) 12.75 V (high-speed program II mode)

ii) Data transfer (copy) (note 1)

In TMP87PH00, EPROM is within the addresses 4000 to 7FFFH. Data is required to be transferred (copied) to the addresses where it is possible to write. The program area in MCU mode and PROM mode is referred to "Program memory area" in Figure 1-1.

Ex. In the block transfer (copy) mode, executed as below.

ROM capacity of 16KB: transferred addresses C000 to FFFFH to addresses 4000 to 7FFFH

iii) Writing address is specified. (Caution 1)

Start address: 4000H End address: 7FFFH

(4) Writing

Writing/Verifying is required to be executed in accordance with PROM programmer operating procedure.

- Note 1: The specifying method is referred to the PROM programmer description. The data in addresses 0000 to 3FFFH must be specified to FFH.
- Note 2: When MCU is set to an adapter or the adapter is set to PROM programmer, a position of pin 1 must be adjusted. If the setting is reversed, MCU, the adapter and PROM program is damaged.
- Note 3:TMP87PH00 does not support the electric signature mode (hereinafter referred to as "signature"). If the signature is used in PROM program, a device is damaged due to applying  $12 \text{ V} \pm 0.5 \text{ V}$  to the address pin 9 (A9). The signature must not be used.

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#### **Electrical Characteristics**

Absolute Maximum Ratings

 $(V_{SS} = 0 V)$ 

Parameter	Symbol	Conditions	Ratings	Unit	
Supply Voltage	$V_{DD}$		– 0.3 to 7	V	
Program Voltage	$V_{PP}$	TEST / VPP	– 0.3 to 13.0	٧	
Input Voltage	$V_{IN}$		– 0.3 to V <sub>DD</sub> + 0.3	>	
Output Voltage	V <sub>OUT1</sub>	P0, P1, P2, P6, P7, XOUT, RESET	– 0.3 to V <sub>DD</sub> + 0.3	v	
	V <sub>OUT2</sub>	P3, P4, P5	- 0.3 to 10	٧	
Output Current (Per 1 pin)	I <sub>OUT1</sub>	P0, P1, P2, P4, P5, P6, P7	3.2	mΑ	
	I <sub>OUT2</sub>	Р3	30	IIIA	
Output Current (Total)	Σ I <sub>OUT1</sub>	P0, P1, P2, P4, P5, P6, P7	120	A	
Output Current (Total)	Σ I <sub>OUT2</sub>	Р3	120	mA	
Davier Dissipation [Tens. 70%]	PD	TMP87PH00N	600		
Power Dissipation [Topr = 70°C]	1 10	TMP87PH00F / PH00DF	350	mW	
Soldering Temperature (time)	Tsld		260 (10 s)	°C	
Storage Temperature	Tstg		– 55 to 125	°C	
Operating Temperature	Topr		– 30 to 70	°C	

Note: The absolute maximum ratings are rated values which must not be exceeded during operation, even for an instant. Any one of the ratings must not be exceeded. If any absolute maximum rating is exceeded, a device may break down or its performance may be degraded, causing it to catch fire or explode resulting in injury to the user. Thus, when designing products which include this device, ensure that no absolute maximum rating value will ever be exceeded.

**Recommended Operating Conditions** 

 $(V_{SS} = 0 \text{ V}, \text{ Topr} = -30 \text{ to } 70^{\circ}\text{C})$ 

Parameter	Symbol	Pins	(	Conditions	Min	Max	Unit
			f. ONUL	NORMAL1, 2 mode	4.5		
			fc = 8 MHz	IDLE1, 2 mode	4.5	6.0	
Supply Voltage			fc = 4.2 MHz	NORMAL1, 2 mode			
	$V_{DD}$		fs = 32.768 kHz	IDLE1, 2 mode	2.7		V
				SLOW mode	7 2.7		
				SLEEP mode			
				STOP mode	2.0		
	V <sub>IH1</sub>	Except hysteresis input		/ > / E \/	$V_{DD} \times 0.70$		
Input High Voltage	V <sub>IH2</sub>	Hysteresis input	V <sub>DD</sub> ≧ 4.5 V		$V_{DD} \times 0.75$	$V_{DD}$	V
	V <sub>IH3</sub>		\	/ <sub>DD</sub> <4.5 V	$V_{DD} \times 0.90$		
	V <sub>IL1</sub>	Except hysteresis input		/ > A E \/		$V_{DD} \times 0.30$	
Input Low Voltage	$V_{IL2}$	Hysteresis input	`	/ <sub>DD</sub> ≧4.5 V	0	$V_{DD} \times 0.25$	٧
	$V_{IL3}$		\	/ <sub>DD</sub> <4.5 V		V <sub>DD</sub> × 0.10	
	fc	XIN, XOUT	V <sub>D</sub>	V <sub>DD</sub> = 4.5 to 6 V		8.0	D d L L
Clock Frequency	ار	AIN, AUUT	V <sub>D</sub>	<sub>D</sub> = 2.7 to 6 V	0.4	4.2	MHz
	fs	XTIN, XTOUT			30.0	34.0	kHz

Note 1: The recommended operating conditions for a device are operating conditions under which it can be guaranteed that the device will operate as specified. If the device is used under operating conditions other than the recommended operating conditions (supply voltage, operating temperature range, specified AC/DC values etc.), malfunction may occur. Thus, when designing products which include this device, ensure that the recommended operating conditions for the device are always adhered to.

Note 2: Clock frequency fc: Supply voltage range is specified in NORMAL mode and IDLE mode.

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D.C. Characteristics

 $(V_{SS} = 0 \text{ V}, \text{ Topr} = -30 \text{ to } 70^{\circ}\text{C})$ 

Parameter	Symbol	Pins	Conditions	Min	Тур.	Max	Unit
Hysteresis Voltage	$V_{HS}$	Hysteresis inputs	V <sub>DD</sub> = 5.0 V	-	0.9	_	V
	I <sub>IN1</sub>	TEST					
Input Current	I <sub>IN2</sub>	Open drain ports, tri-state ports	V <sub>DD</sub> = 5.5 V V <sub>IN</sub> = 5.5 V / 0 V	_	_	± 2	μΑ
	I <sub>IN3</sub>	RESET, STOP	VDD = 5.0 V       -       0.9       -         VDD = 5.5 V       -       -       ± 2         VDD = 5.5 V       100       220       450         VDD = 5.5 V       -       -       2         VDD = 5.5 V       -       -       2         VDD = 5.5 V       -       -       -       ± 2         VDD = 4.5 V       10H = -0.7mA       4.1       -       -       -         VDD = 4.5 V       10L = 1.6 mA       -       -       0.4         VDD = 4.5 V       -       0.4       -       -       -         VDD = 5.5 V       -       8.5       12       -         fc = 8 MHz       -       8.5       12       -         fc = 8 MHz       -       3.5       5         VDD = 3.0 V       VIN = 2.8 V / 0.2 V       -       2.5       3.5         VDD = 3.0 V       -       30       60         fs = 32.768 kHz       -       15       30         VDD = 3.0 V       -       15       30				
Input Resistance	R <sub>IN2</sub>	RESET	V <sub>DD</sub> = 5.0 V	100	220	450	kΩ
Output Leakage	I <sub>LO1</sub>	Sink open drain ports	$V_{DD} = 5.5 \text{ V}, V_{OUT} = 5.5 \text{ V}$	_	_	2	
Current	I <sub>LO2</sub>	Tri-state ports	$V_{DD} = 5.5 \text{ V}, V_{OUT} = 5.5 \text{ V} / 0 \text{ V}$	-	_	± 2	μA
Output High Voltage	V <sub>OH2</sub>	Tri- state ports	$V_{DD} = 4.5 \text{ V}, I_{OH} = -0.7 \text{mA}$	4.1	_	_	V
Output Low Voltage	$V_{OL}$	Except XOUT and P3	$V_{DD} = 4.5 \text{ V}, I_{OL} = 1.6 \text{ mA}$	-	_	0.4	V
Output Low Current	I <sub>OL3</sub>	Port P3	$V_{DD} = 4.5 \text{ V}, V_{OL} = 1.0 \text{ V}$	_	20	_	mA
Supply Current in NORMAL 1, 2 modes				-	8.5	12	mA
Supply Current in IDLE 1, 2 modes			$V_{DD} = 4.5 \text{ V}, V_{OL} = 1.0 \text{ V}$ $V_{DD} = 5.5 \text{ V}$ $fc = 8 \text{ MHz}$ $fs = 32.768 \text{ kHz}$	-	3.5	5	mA
Supply Current in NORMAL 1, 2 modes				-	2.5	3.5	mA
Supply Current in IDLE 1, 2 modes	I <sub>DD</sub>			-	1.5	2.0	mA
Supply Current in SLOW mode			1 55	-	30	60	μΑ
Supply Current in SLEEP mode				_	15	30	μΑ
Supply Current in STOP mode			V <sub>DD</sub> = 5.5 V V <sub>IN</sub> = 5.3 V / 0.2 V	-	0.5	10	μΑ

Note 1: Typical value show those at Topr =  $25^{\circ}$ C.

Note 2: Input Current  $I_{IN1}$ ,  $I_{IN3}$ ; The current through resistor is not included, when the input resistor (pull-up or pull-down) is contained.

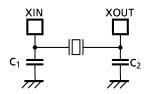
#### A.C. Characteristics

 $(V_{SS} = 0 \text{ V}, V_{DD} = 4.5 \text{ to } 6.0 \text{ V}, Topr = -30 \text{ to } 70^{\circ}\text{C})$ 

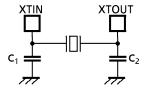
Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
		In NORMAL1, 2 modes	0.5		10	
Machine Cycle Time		In IDLE1, 2 modes	0.5	_	10	
	t <sub>cy</sub>	In SLOW mode	117.6		122.2	μs
		In SLEEP mode	117.6	_	133.3	
High Level Clock Pulse Width	t <sub>WCH</sub>	For external clock operation	F0			
Low Level Clock Pulse Width	t <sub>WCL</sub>	(XIN input), fc = 8 MHz	50	_	_	ns
High Level Clock Pulse Width	t <sub>WSH</sub>	For external clock operation	14.7			
Low Level Clock Pulse Width	t <sub>WSL</sub>	(XTIN input), fs = 32.768 kHz	14.7	_	_	μS

## Recommended Oscillating Conditions $(V_{SS} = 0 \text{ V}, V_{DD} = 4.5 \text{ to } 6.0 \text{ V}, \text{ Topr} = -30 \text{ to } 70^{\circ}\text{C})$

Parameter	Oscillator	Oscillation	ecommended Oscillator		Recommended Constant		
Tarameter	Oscillator	Frequency	ecommend	ded Oscillator	C <sub>1</sub>	C <sub>2</sub>	
	Ceramic Resonator		KYOCERA	KBR8.0M	30 pF	30 pF	
	Ceramic Resonator	4 MHz	KYOCERA	KBR4.0MS	30 βι	30 pi	
High-frequency		4 101112	MURATA	CSA4.00MG			
Oscillation		8 MHz	тоуосом	210B 8.0000	20. 5		
	Crystal Oscillator	4 MHz	тоуосом	204B 4.0000	20 pF	20 pF	
Low-frequency Oscillation	Crystal Oscillator	32.768 kHz	NDK	MX-38T	15 pF	15 pF	



(1) High-frequency Oscillation



(2) Low-frequency Oscillation

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Note: When used in high electric field such as a picture tube, the package is recommended to be electrically shielded to maintain a regular operation.

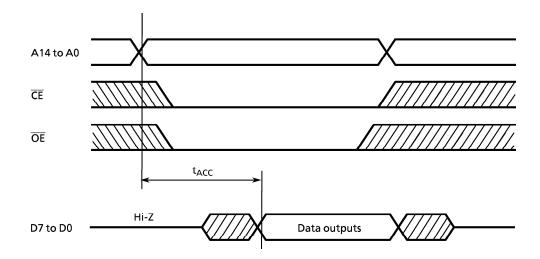
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D.C./A.C. Characteristics (PROM mode) (V<sub>SS</sub> = 0 V)

# (1) Read Operation (Topr = $-30 \text{ to } 70^{\circ}\text{C}$ )

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		V <sub>CC</sub> × 0.7	ı	V <sub>CC</sub>	٧
Input Low Voltage	$V_{IL4}$		0	ı	V <sub>CC</sub> × 0.12	٧
Power Supply Voltage	V <sub>CC</sub>		4.75	5.00	5.25	.,
Program Power Supply Voltage	V <sub>PP</sub>		V <sub>CC</sub> – 0.6	V <sub>CC</sub>	V <sub>CC</sub> + 0.6	V
Address Access Time	t <sub>ACC</sub>	V <sub>CC</sub> = 5.0 ± 0.25 V	_	1.5 tcyc + 300	_	ns

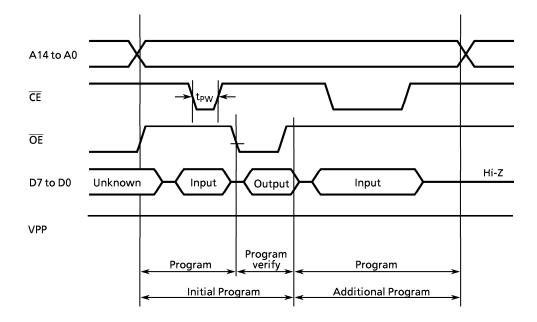
Note: tcyc = 500 ns at 8 MHz



Timing Waveforms of Read Operation

## (2) Program Operation (High-Speed Write Mode - I ) (Topr = $25 \pm 5$ °C)

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		V <sub>CC</sub> × 0.7	1	V <sub>CC</sub>	٧
Input Low Voltage	$V_{IL4}$		0	1	V <sub>CC</sub> × 0.12	>
Power Supply Voltage	V <sub>CC</sub>		5.75	6.0	6.25	<
Program Power Supply Voltage	$V_{PP}$		12.0	12.5	13.0	<
Initial Program Pulse Width	t <sub>PW</sub>	$V_{CC} = 6.0 \text{ V} \pm 0.25 \text{ V}$ $V_{PP} = 12.5 \pm 0.5 \text{ V}$	0.95	1.0	1.05	ms

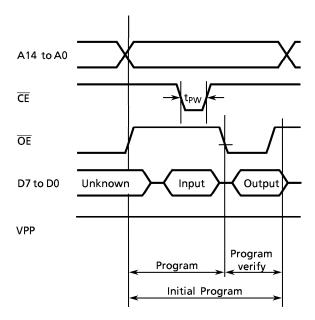


**Timing Waveforms of Programming Operation** 

- Note 1: When  $V_{cc}$  power supply is turned on or after,  $V_{pp}$  must be increased. When  $V_{cc}$  power supply is turned off or before,  $V_{pp}$  must be decreased.
- Note 2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.5 V  $\pm$  0.5 V) to the V<sub>pp</sub> pin as the device is damaged.
- Note 3: Be sure to execute the recommended programing mode with the recommended programing adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.

## (3) Program Operation (High speed write mode -II) (Topr = $25 \pm 5$ °C)

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		$V_{CC} \times 0.7$	-	V <sub>CC</sub>	٧
Input Low Voltage	$V_{IL4}$		0	1	$V_{CC} \times 0.12$	٧
Supply Voltage	$V_{CC}$		6.00	6.25	6.50	٧
Program Supply Voltage	$V_{PP}$		12.50	12.75	13.0	٧
Initial Program Pulse Width	t <sub>PW</sub>	$V_{CC} = 6.25 \text{ V} \pm 0.25 \text{ V},$ $V_{PP} = 12.75 \text{ V} \pm 0.25 \text{ V}$	0.095	0.1	0.105	ms



- Note 1: When  $V_{cc}$  power supply is turned on or after,  $V_{pp}$  must be increased. When  $V_{cc}$  power supply is turned off or before,  $V_{pp}$  must be decreased.
- Note 2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.75 V  $\pm$  0.25 V) to the V<sub>pp</sub> pin as the device is damaged.
- Note 3: Be sure to execute the recommended programing mode with the recommended programing adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.

#### **Electrical Characteristics**

Absolute Maximum Ratings

 $(V_{SS} = 0 V)$ 

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	$V_{DD}$		- 0.3 to 6.5	V
Program Voltage	V <sub>PP</sub>	TEST / VPP pin	- 0.3 to 13.0	V
Input Voltage	V <sub>IN</sub>		- 0.3 to V <sub>DD</sub> + 0.3	V
Output Voltage	V <sub>OUT</sub>		- 0.3 to V <sub>DD</sub> + 0.3	V
Output Current (Per 1 pin)	I <sub>OUT1</sub>	Ports P0, P1, P2, P4, P5, P6, P7	3.2	
	I <sub>OUT2</sub>	Port P3	30	mA
0.1.15	Σ I <sub>OUT1</sub>	Ports P0, P1, P2, P4, P5, P6, P7	120	
Output Current (Total)	Σ I <sub>OUT2</sub>	Port P3	120	mA
Power Dissipation [Topr = 70°C]	PD		350	mW
Soldering Temperature (time)	Tsld		260 (10 s)	°C
Storage Temperature	Tstg		– 55 to 125	°C
Operating Temperature	Topr		- 30 to 70	°C

Note: The absolute maximum ratings are rated values which must not be exceeded during operation, even for an instant. Any one of the ratings must not be exceeded. If any absolute maximum rating is exceeded, a device may break down or its performance may be degraded, causing it to catch fire or explode resulting in injury to the user. Thus, when designing products which include this device, ensure that no absolute maximum rating value will ever be exceeded.

Recommended Operating Conditions

 $(V_{SS} = 0 \text{ V, Topr} = -30 \text{ to } 70^{\circ}\text{C})$ 

Parameter	Symbol	Pins	c	Conditions	Min	Max	Unit
			C. OBALL	NORMAL1, 2 mode	4.5		
			fc = 8 MHz	IDLE1, 2 mode	4.5		
Supply Voltage			f- 4.2 NALL-	NORMAL1, 2 mode			
	$V_{DD}$		fc = 4.2 MHz	IDLE1, 2 mode		5.5	V
				SLOW mode	1.8		
			32.768 kHz	SLEEP mode			
				STOP mode			
	V <sub>IH1</sub>	Except Hysteresis inputs	V <sub>DD</sub> ≥ 4.5 V V <sub>DD</sub> < 4.5 V		$V_{DD} \times 0.7$	V <sub>DD</sub>	
Input High Voltage	V <sub>IH2</sub>	Hysteresis inputs			$V_{DD} \times 0.75$		V
	V <sub>IH3</sub>				$V_{DD} \times 0.90$		
	$V_{IL1}$	Except Hysteresis inputs		> 1 = 1/		$V_{DD} \times 0.28$	
Input Low Voltage	$V_{IL2}$	Hysteresis inputs	v	<sub>DD</sub> ≧ 4.5 V	0	$V_{DD} \times 0.25$	V
	$V_{IL3}$		V	<sub>'DD</sub> <4.5 V		V <sub>DD</sub> × 0.10	
	fc	VIN VOLIT	V <sub>DD</sub> = 4.5 to 5.5 V		0.4	8.0	MHz
Clock Frequency	IC IC	XIN, XOUT	V <sub>DD</sub> = 1.8 to 4.5 V		0.4	4.2	
	fs	XTIN, XOUT			30.0	34.0	kHz

Note: The recommended operating conditions for a device are operating conditions under which it can be guaranteed that the device will operate as specified. If the device is used under operating conditions other than the recommended operating conditions (supply voltage, operating temperature range, specified AC/DC values etc.), malfunction may occur. Thus, when designing products which include this device, ensure that the recommended operating conditions for the device are always adhered to.

#### D.C. Characteristics

 $(V_{SS} = 0 \text{ V}, T_{opr} = -30 \text{ to } 70^{\circ}\text{C})$ 

Parameter	Symbol	Pins	Conditions	Min	Тур.	Max	Unit	
Hysteresis Voltage	V <sub>HS</sub>	Hysteresis inputs	V <sub>DD</sub> = 5.0 V	-	0.9	-	٧	
Input Current	I <sub>IN1</sub>	TEST  Open drain ports and tri-state ports	V <sub>DD</sub> = 5.5 V V <sub>IN</sub> = 5.5 V / 0 V	_	_	± 2	μΑ	
	I <sub>IN3</sub>	RESET, STOP	† ""				·	
Input Low Current	I <sub>IL</sub>	Push-pull ports $V_{DD} = 5.5 \text{ V}, V_{IN} = 0.4 \text{ V}$		_	_	- 2	mA	
	R <sub>IN1</sub>	Port P7 with pull-up	V <sub>DD</sub> = 5.0 V	30	70	150		
Input Resistance	R <sub>IN2</sub>	RESET	V <sub>DD</sub> = 5.0 V	100	220	450	kΩ	
Output Leakage	I <sub>LO1</sub>	Open drain ports	V <sub>DD</sub> = 5.5 V, V <sub>OUT</sub> = 5.5 V	-	-	2		
Current	I <sub>LO2</sub>	Tri-state ports	$V_{DD} = 5.5 \text{ V}, V_{OUT} = 5.5 \text{ V} / 0 \text{ V}$	_	_	± 2	$\mu$ A	
	V <sub>OH1</sub>	Push-pull ports	$V_{DD} = 4.5 \text{ V}, \ I_{OH} = -200 \ \mu\text{A}$	2.4	_	_		
	V <sub>OH2</sub>	Tri- state ports	$V_{DD} = 4.5 \text{ V}, I_{OH} = -0.7 \text{ mA}$	4.1	_	_		
Output High Voltage	V <sub>OH3</sub>	Push- pull ports	$V_{DD} = 1.8 \text{ V}, I_{OH} = -5 \mu A$ 1.		-	-	,	
Output Low Voltage	V <sub>OH4</sub>	Tri- state ports	$V_{DD} = 1.8 \text{ V}, I_{OH} = -10 \mu \text{A}$	1.6	-	-	V	
	V <sub>OL1</sub>	Except XOUT and port P3	$V_{DD} = 4.5 \text{ V, } I_{OL} = 1.6 \text{ mA}$	-	-	0.4		
	V <sub>OL2</sub>	Except XOUT	$V_{DD} = 1.8 \text{ V}, I_{OL} = 20 \mu A$	-	-	0.2		
Output Low Current	I <sub>OL3</sub>	Port P3	$V_{DD} = 4.5 \text{ V}, V_{OL} = 1.0 \text{ V}$	_	20	_		
Supply Current in NORMAL 1 , 2 mode			V <sub>DD</sub> = 5.5 V fc = 8 MHz	-	7.0	10		
Supply Current in IDLE 1, 2 mode			fs = 32.768 kHz V <sub>IN</sub> = 5.3 V / 0.2 V	_	3.5	5		
Supply Current in NORMAL 1 , 2 mode			V <sub>DD</sub> = 3.0 V fc = 4.19 MHz fs = 32.768 kHz V <sub>IN</sub> = 2.8 V / 0.2 V	-	2.5	3.5	mA	
Supply Current in IDLE 1, 2 mode				_	1.5	2.0		
Supply Current in NORMAL 1 , 2 mode			V <sub>DD</sub> = 1.8 V fc = 4.19 MHz	_	1.0	2.0		
Supply Current in IDLE 1, 2 mode	I <sub>DD</sub>		fs = 32.768 kHz V <sub>IN</sub> = 1.7 V / 0.1V	_	0.5	1.0		
Supply Current in SLOW mode			V <sub>DD</sub> = 3.0 V	_	30	60		
Supply Current in SLEEP mode			fs = 32.768 kHz V <sub>IN</sub> = 2.8 V / 0.2 V	_	15	30		
Supply Current in SLOW mode			V <sub>DD</sub> = 1.8 V	_	15	30	μΑ	
Supply Current in SLEEP mode			fs = 32.768 kHz V <sub>IN</sub> = 1.7 V / 0.1V	_	10	20		
Supply Current in STOP mode			V <sub>DD</sub> = 5.5 V V <sub>IN</sub> = 5.3 V / 0.2 V	_	0.5	10		

Note 1: Typical values show those at  $Topr = 25^{\circ}C$ ,  $V_{DD} = 3V$ .

Note 2: Input Current; The current through pull-up or pull-down resistor is not included.

#### A.C. Characteristics

 $(V_{SS} = 0 \text{ V}, V_{DD} = 4.5 \text{ to } 5.5 \text{ V}, Topr = -30 \text{ to } 70^{\circ}\text{C})$ 

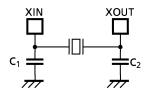
Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Machine Cycle Time	t <sub>cy</sub>	In NORMAL 1, 2 mode	0.5	_	10	μ\$
		In IDLE 1, 2 mode				
		In SLOW mode	117.6	_	133.3	
		In SLEEP mode				
High Level Clock Pulse Width	t <sub>WCH</sub>	For external clock operation	50	_		
Low Level Clock Pulse Width	t <sub>WCL</sub>	(XIN input) , fc = 8.4 MHz			_	ns
High Level Clock Pulse Width	t <sub>WSH</sub>	For external clock operation	14.7			
Low Level Clock Pulse Width	t <sub>WSL</sub>	(XTIN input), fs = 32.768 kHz		ı	ı	μS

# $(V_{SS} = 0 \text{ V}, V_{DD} = 1.8 \text{ to } 4.5 \text{ V}, Topr = -30 \text{ to } 70^{\circ}\text{C})$

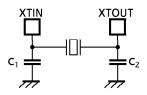
Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Machine Cycle Time	t <sub>cy</sub>	In NORMAL 1, 2 mode	0.05	-	10	· μs
		In IDLE 1, 2 mode	0.95			
		In SLOW mode	117.6	_	133.3	
		In SLEEP mode				
High Level Clock Pulse Width	t <sub>WCH</sub>	For external clock operation	110	_	_	ns
Low Level Clock Pulse Width	t <sub>WCL</sub>	(XIN input), fc = 4.2 MHz				
High Level Clock Pulse Width	t <sub>WSH</sub>	For external clock operation	14.7	_	_	
Low Level Clock Pulse Width	t <sub>WSL</sub>	(XTIN input), fs = 32.768 kHz				$\mu$ S

# Recommended Oscillating Conditions ( $V_{SS} = 0 \text{ V}, T_{opr} = -30 \text{ to } 70^{\circ}\text{C}$ )

Davameter	On sill at a m	Oscillation		and and Operithe to a	Recommended Constant		
Parameter Oscillator		Frequency	ecomme	nded Oscillator	C <sub>1</sub>	C <sub>2</sub>	
		4.19 MHz	MURATA	CSA4.19MG	30 pF	30 pF	
High-frequency	Ceramic Resonator	(VDD = 1.8 to 5.5 V)	MURATA	CST4.19MGW	_	-	
		8 MHz	MURATA	CSA8.00MTZ	15 pF	15 pF	
		(VDD = 4.5  to  5.5  V)	MURATA	CST8.00MTW	_	_	
	Crystal Oscillator	8 MHz (VDD = 4.5 to 5.5 V)	NDK	AT-51	16 pF	16 pF	
Low-frequency	Crystal Oscillator	32.768 kHz (VDD = 1.8 to 5.5 V)	NDK	MX-38T	12 pF	12 pF	







(2) Low-frequency Oscillation

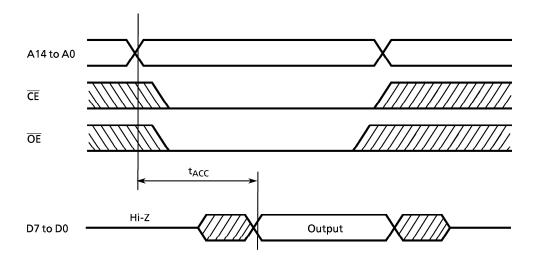
Note: When used in high electric field such as a picture tube, the package is Recommended to be electrically shielded to maintain a regular operation.

D.C./A.C. Characteristics (PROM mode) (V<sub>SS</sub> = 0 V)

# (1) Read Operation (Topr = $-30 \text{ to } 70 ^{\circ}\text{C}$ )

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		V <sub>CC</sub> × 0.7	_	V <sub>CC</sub>	٧
Input Low Voltage	V <sub>IL4</sub>		0	_	V <sub>CC</sub> × 0.12	>
Power Supply Voltage	V <sub>CC</sub>		4.75	5.00	5.25	\ \
Program Power Supply Voltage	V <sub>PP</sub>		V <sub>CC</sub> – 0.6	V <sub>CC</sub>	V <sub>CC</sub> + 0.6	v
Address Access Time	t <sub>ACC</sub>	V <sub>CC</sub> = 5.0 ± 0.25 V	_	1.5 tcyc + 300	_	ns

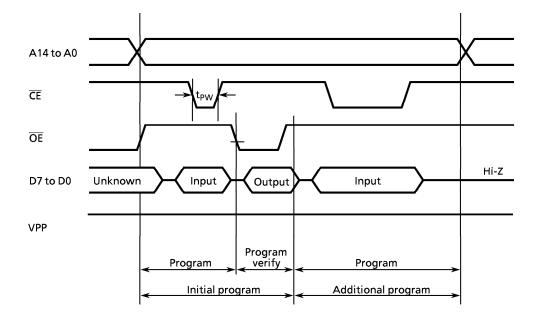
Note: tcyc = 500 ns at 8 MHz



**Timing Waveforms of Read Operation** 

## (2) Program Operation (High-Speed Write Mode - I ) (Topr = $25 \pm 5$ °C)

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		V <sub>CC</sub> × 0.7	-	V <sub>CC</sub>	٧
Input Low Voltage	$V_{IL4}$		0	ı	V <sub>CC</sub> × 0.12	>
Power Supply Voltage	V <sub>CC</sub>		5.75	6.0	6.25	<
Program Power Supply Voltage	$V_{PP}$		12.0	12.5	13.0	<
Initial Program Pulse Width	t <sub>PW</sub>	$V_{CC} = 6.0 \text{ V} \pm 0.25 \text{ V}$ $V_{PP} = 12.5 \text{ V} \pm 0.5 \text{ V}$	0.95	1.0	1.05	ms



**Timing Waveforms of Programming Operation** 

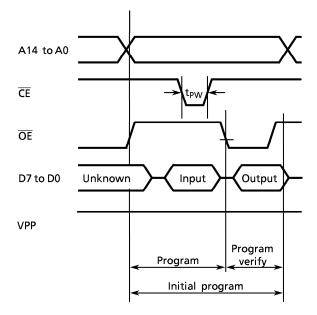
Note1: When  $V_{cc}$  power supply is turned on or after,  $V_{pp}$  must be increased. When  $V_{cc}$  power supply is turned off or before,  $V_{pp}$  must be decreased.

Note2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.5 V  $\pm$  0.5 V) to the  $V_{pp}$  pin as the device is damaged.

Note3: Be sure to execute the Recommended programing mode with the Recommended programing adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.

## (3) Program Operation (High speed write mode -II) (Topr = $25 \pm 5$ °C)

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Input High Voltage	V <sub>IH4</sub>		$V_{CC} \times 0.7$	-	V <sub>CC</sub>	V
Input Low Voltage	$V_{IL4}$		0	1	$V_{CC} \times 0.12$	V
Supply Voltage	V <sub>CC</sub>		6.00	6.25	6.50	V
Program Supply Voltage	V <sub>PP</sub>		12.50	12.75	13.0	V
Initial Program Pulse Width	t <sub>PW</sub>	$V_{CC} = 6.25 \text{ V} \pm 0.25 \text{ V},$ $V_{PP} = 12.75 \text{ V} \pm 0.25 \text{ V}$	0.095	0.1	0.105	ms



Note1: When  $V_{cc}$  power supply is turned on or after,  $V_{pp}$  must be increased. When  $V_{cc}$  power supply is turned off or before,  $V_{pp}$  must be decreased.

Note2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.75 V  $\pm$  0.25 V) to the  $V_{pp}$  pin as the device is damaged.

Note3: Be sure to execute the Recommended programing mode with the Recommended programing adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.